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(54) Title: METHOD OF MAKING MULTIPLE IMPLANTATIONS IN A SUBSTRATE

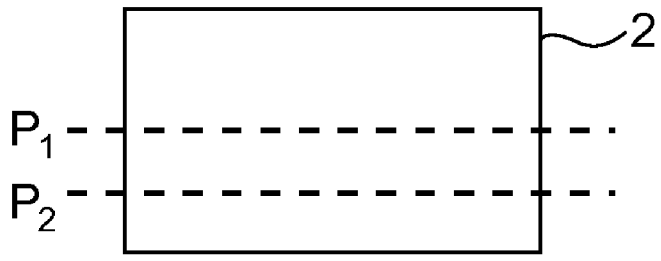


FIG.1

(57) Abstract: The invention relates to a method of implanting atoms and/or ions into a substrate, comprising: a) a first implantation of ions or atoms at a first depth in the substrate, in order to form a first implantation plane, b) at least one second implantation of ions or atoms at a second depth in the substrate, which is different from the first depth, in order to form at least one second implantation plane.